



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate Transistors

KTA2015 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 0.1 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -35 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-323

1. BASE
2. EMITTER
3. COLLECTOR



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-35V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100mA$	70		240	
	$h_{FE(2)}$	$V_{CE}=-6V, I_C=-400mA$ O Y	25 40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-0.25	V
Base-emitter voltage	V_{BE}	$V_{CE}=-1V, I_C=-100mA$			-1	V
Transition frequency	f_T	$V_{CE}=-6V, I_C=-20mA$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-6V, I_E=0, f=1MHz$		13		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	70-140	120-240
Marking	ZO	ZY